NDFP03N150C

N-Channel Power MOSFET 1500V, 2.5A, 10.5Ω, TO-220F-3FS

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TO-220F-3FS

Features

- On-resistance $R_{DS}(on)=8\Omega(typ.)$
- Input Capacitance Ciss=650pF(typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	V _{DSS}		1500	V
Gate to Source Voltage	VGSS		±30	V
Drain Current (DC)	ID		2.5	Α
Drain Current (DC) Limited by Package	I _{DL}		2	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	5	Α
Allowable Power Dissipation	PD		2	W
		Tc=25°C	32	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		- 55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		20	mJ
Avalanche Current *2	IAV		2	Α

^{*1} V_{DD}=50V, L=10mH, I_{AV}=2A (Fig.1)

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			11.7
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =10mA, V _{GS} =0V	1500			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1200V, V _{GS} =0V			1	mA
Gate to Source Leakage Current	IGSS	VGS=±30V, VDS=0V			±100	nA
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	2		4	٧
Forward Transfer Admittance	yfs	V _{DS} =20V, I _D =1A		1.9		S
Static Drain to Source On-State Resistance	R _{DS} (on)	I _D =1A, V _{GS} =10V		8	10.5	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		650		pF
Output Capacitance	Coss			70		pF
Reverse Transfer Capacitance	Crss			20		pF
Turn-ON Delay Time	t _d (on)	0.5		15		ns
Rise Time	t _r			20		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		148		ns
Fall Time	tf			44		ns

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ORDERING INFORMATION

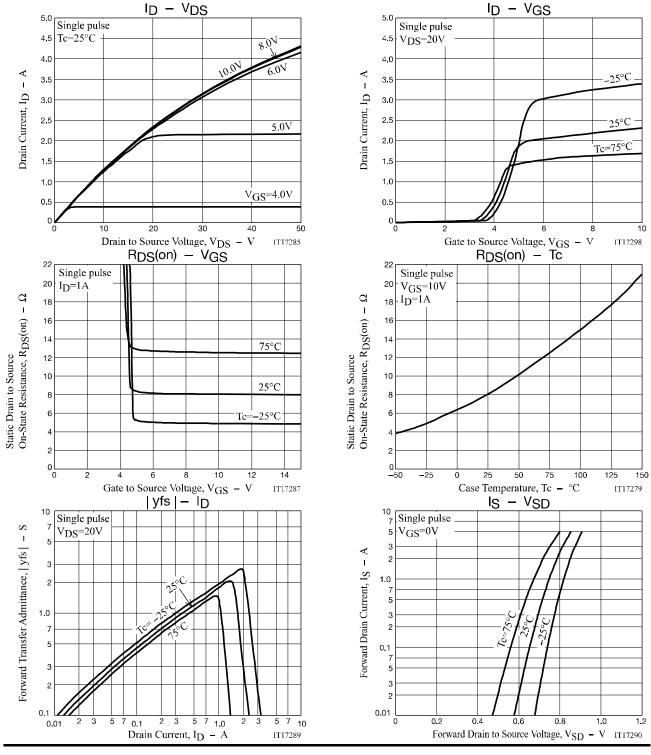
See detailed ordering and shipping information on page 4 of this data sheet.

^{*2} L≤10mH, Single Pulse

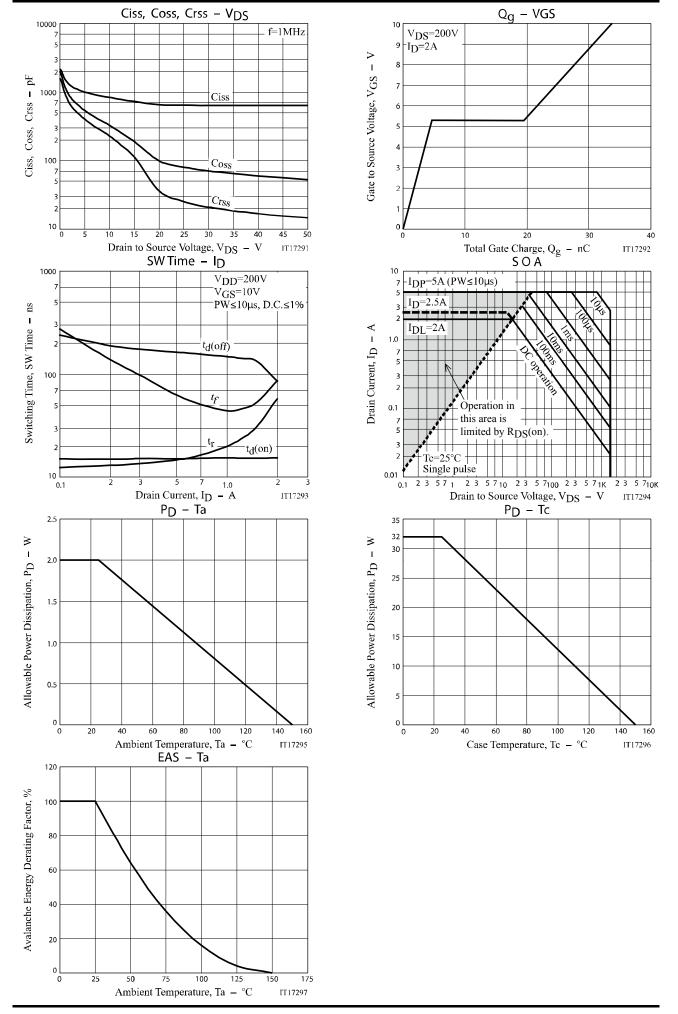
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Total Gate Charge	Qg		34		nC
Gate to Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =2A	4.7		nC
Gate to Drain "Miller" Charge	Qgd		15		nC
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0V	0.78	1.5	٧
Reverse Recovery Time	trr	See Fig.3	300		ns
Reverse Recovery Charge	Qrr	IS=2A, VGS=0V, di/dt=100A/μs	1900		nC



NDFP03N150C



Package Dimensions

NDFP03N150CG

TO-220F-3FS

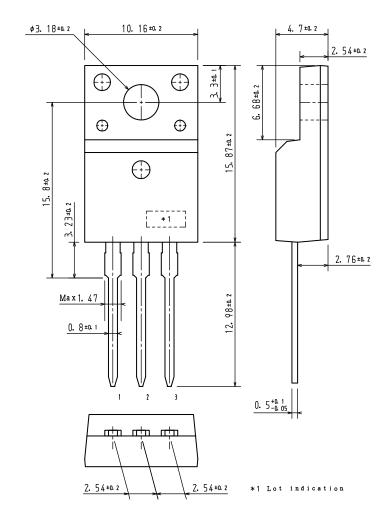
CASE 221AM ISSUE O

Unit : mm

1: Gate

2: Drain

3: Source



Ordering & Package Information

Device	Package	Shipping	note
NDFP03N150CG	TO-220F-3FS SC-67,	50 pcs. / tube	Pb-Free

Marking



Electrical Connection

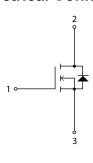


Fig.1 Unclamped Inductive Switching Test Circuit

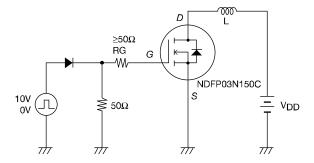


Fig.2 Switching Time Test Circuit

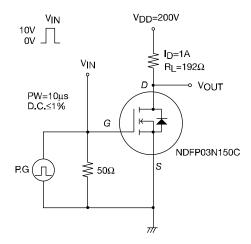
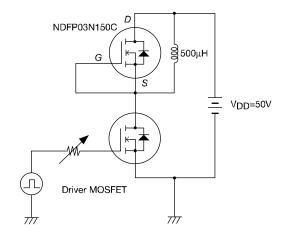


Fig.3 Reverse Recovery Time Test Circuit



Note on usage: Since the NDFP03N150C is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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